



DOCUMENT CHANGE REQUEST

DCR number 517 Changes required for: General

Date: 2009/05/06

Date sent: 2009/05/06

Originator: S Jeffery - ESCC

Organisation: ESA/ESTEC

Status: IMPLEMENTED

Title: Transistors Silicon Switching PNP, based on type 2N3467

Number: 5208/009

Issue: 2

Other documents affected:

Page:

See attachment

Paragraph:

See attachment

Original wording:

Proposed wording:

Update the Maximum Ratings table (see the attachment for details) so that this detail spec is clear, complete and the content and format is in-line with other detail specifications for similar Part Types.

Justification:

Improve the content and clarity of the spec.

Attachments:

5208009_Issue_3_-_Draft_A.pdf, null

Modifications:

N/A

Approval signature:

Date signed:

2009-05-06



Pages 1 to 13

TRANSISTORS, SWITCHING, PNP

BASED ON TYPE 2N3467

ESCC Detail Specification No. 5208/009

as applicable

| | |
|-------------------|-------------------------|
| Issue 3 - Draft A | October 2008 |
|-------------------|-------------------------|



Document Custodian: European Space Agency - see <https://escies.org>



as applicable

LEGAL DISCLAIMER AND COPYRIGHT

European Space Agency, Copyright © 2008. All rights reserved.

The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or alleged to be caused, directly or indirectly by the use and application of this ESCC publication.

This publication, without the prior permission of the European Space Agency and provided that it is not used for a commercial purpose, may be:

- copied in whole, in any medium, without alteration or modification.
- copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.



DOCUMENTATION CHANGE NOTICE

(Refer to <https://escies.org> for ESCC DCR content)

| DCR No. | CHANGE DESCRIPTION |
|---------|---|
| 333 | Specification up issued to incorporate editorial and technical changes per DCR. |

t6d

At $T_{case} \leq +25^{\circ}C$

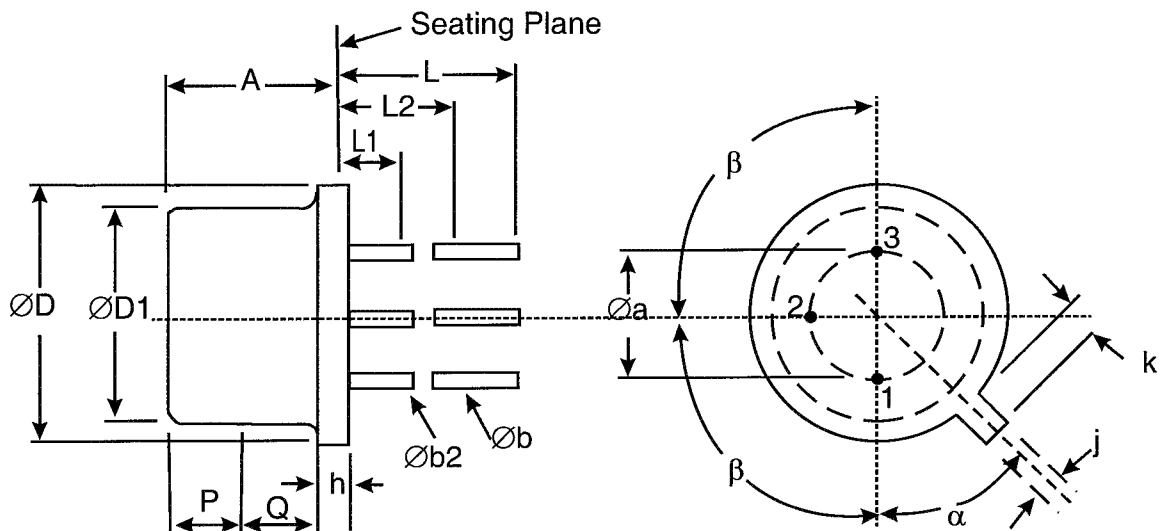
| Characteristics | Symbols | Maximum Ratings | Unit | Remarks |
|-----------------------------|------------|-----------------|-------------|---|
| Collector-Base Voltage | V_{CBO} | -40 | V | Over entire operating temperature range |
| Collector-Emitter Voltage | V_{CEO} | -40 | V | |
| Emitter-Base Voltage | V_{EBO} | -5 | V | |
| Collector Current | I_C | -1 | A | Continuous |
| Power Dissipation | P_{tot1} | 1 | W | At $T_{amb} \leq +25^{\circ}C$ |
| | P_{tot2} | 5 | W | Note 1 |
| Operating Temperature Range | T_{op} | -65 to +200 | $^{\circ}C$ | Note 1 |
| Storage Temperature Range | T_{stg} | -65 to +200 | $^{\circ}C$ | Note 1 |
| Soldering Temperature | T_{sol} | +265 | $^{\circ}C$ | Note 2 |

NOTES:

- For $T_{amb} > +25^{\circ}C$, derate linearly to 0W at $+200^{\circ}C$.
- For Variants with tin-lead plating or hot solder dip lead finish all testing performed at $T_{amb} > +125^{\circ}C$ shall be carried out in a 100% inert atmosphere.
- Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

1.6 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.6.1 Metal Can Package (TO-39) - 3 lead



| Symbols | Dimensions mm | | Notes |
|---------|---------------|-------|-------|
| | Min | Max | |
| Øa | 4.83 | 5.35 | |
| A | 6 | 6.6 | |
| Øb | 0.4 | 0.533 | 2, 3 |
| Øb2 | 0.4 | 0.483 | 2, 3 |

| | | | | |
|--|---------------|-----|------|--|
| Thermal Resistance, Junction-to-Ambient | $R_{th(j-a)}$ | 175 | °C/W | |
| Thermal Resistance, Junction-to-Case | $R_{th(j-c)}$ | 30 | °C/W | |